

UNISONIC TECHNOLOGIES CO., LTD

UT3413 Power MOSFET

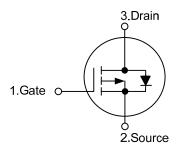
P-CHANNEL ENHANCEMENT MODE

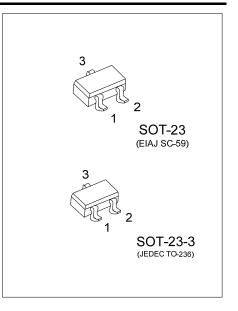
■ DESCRIPTION

The UTC **UT3413** is P-channel enhancement mode Power MOSFET, designed with high density cell, with fast switching speed, low on-resistance, excellent thermal and electrical capabilities and operation with low gate voltages.

This device is suitable for use as a load switch or in PWM applications.

■ SYMBOL

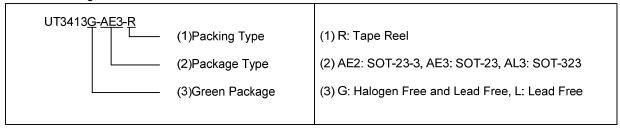




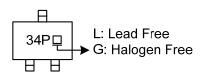
ORDERING INFORMATION

Ordering Number		Doolsons	Pin Assignment			Deskins	
Lead Free	Halogen Free	Package	1	2	3	Packing	
UT3413L-AE2-R	UT3413G-AE2-R	SOT-23-3	G	S	D	Tape Reel	
UT3413L-AE3-R	UT3413G-AE3-R	SOT-23	G	S	D	Tape Reel	

Note: Pin Assignment: G: Gate S: Source D: Drain



MARKING



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UT3413 Power MOSFET

■ **ABSOLUTE MAXIMUM RATINGS** (T_A=25°C, unless otherwise specified)

PARAMETER	SYMBOL	RATING	UNIT
Drain-Source Voltage	V_{DSS}	-20	V
Gate-Source Voltage	V_{GSS}	±8	V
Continuous Drain Current (Note 3)	I_{D}	-3	Α
Pulsed Drain Current (Note 1, 2)	I _{DM}	-15	Α
Power Dissipation	P_{D}	0.6	W
Junction Temperature	T_J	+150	°C
Storage Temperature	T_{STG}	-55 ~ + 150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

PARAMETER	SYMBOL	RATING	UNIT
Junction to Ambient	θ_{JA}	208	°C/W

Note: Surface mounted on 1 in² copper pad of FR4 board.

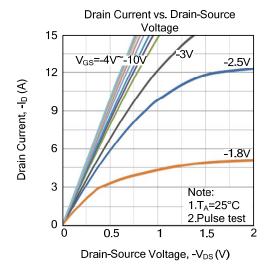
■ **ELECTRICAL CHARACTERISTICS** (T_J=25°C, unless otherwise specified)

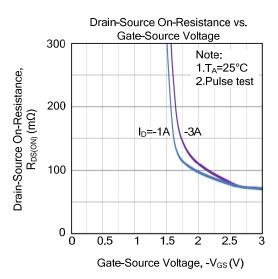
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV_{DSS}	V _{GS} =0V, I _D =-250μA	-20			V	
Drain-Source Leakage Current	I_{DSS}	V _{DS} =-16V, V _{GS} =0V			-1	μΑ	
Gate-Source Leakage Current	I_{GSS}	V _{DS} =0V, V _{GS} =±8.0V			±100	nA	
ON CHARACTERISTICS							
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}$, $I_D=-250\mu A$	-0.3		-1.0	V	
Drain Course On State Resistance		V_{GS} =-4.5V, I_{D} =-3.0A			97	mΩ	
Drain-Source On-State Resistance	R _{DS(ON)}	V_{GS} =-2.5V, I_{D} =-2.6A			130	mΩ	
(Note 2)		V _{GS} =-1.8V, I _D =-1.0A			190	mΩ	
DYNAMIC PARAMETERS							
Input Capacitance	C_{ISS}			616		pF	
Output Capacitance	Coss	V_{DS} =-10 V, V_{GS} =0V, f=1MHz		127		pF	
Reverse Transfer Capacitance	C_{RSS}			99.4		рF	
SWITCHING PARAMETERS							
Total Gate Charge (Note 2)	Q_{G}			8.6		nC	
Gate-Source Charge	Q_GS	V_{DS} =-10V, V_{GS} =-4.5V, I_{D} =-3.0A		1.4		nC	
Gate-Drain Charge	Q_GD			2.3		nC	
Turn-ON Delay Time (Note 2)	$t_{D(ON)}$			5.6		ns	
Turn-ON Rise Time	t_R	V_{GS} =-4.5V, V_{DS} =-10V, R_L =3.3 Ω ,		17.5		ns	
Turn-OFF Delay Time	t _{D(OFF)}	R_{GEN} =3 Ω		32		ns	
Turn-OFF Fall Time	t_{F}			24		ns	
SOURCE- DRAIN DIODE RATINGS AN	D CHARACTI	ERISTICS					
Maximum Continuous Drain-Source					-3	Α	
Diode Forward Current	I _S				-ა	А	
Drain-Source Diode Forward	V_{SD}	I _S =-1.0A, V _{GS} =0V			-1	V	
Voltage(Note2)	V SD	151.0A, VGS-0V			- 1	V	

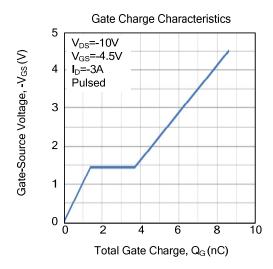
Notes: 1. Repetitive Rating: Pulse width limited by maximum junction temperature.

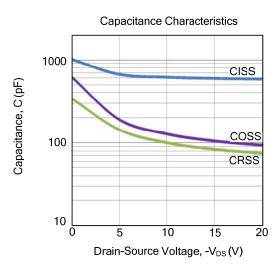
2. Pulse width \leq 300 μ s, duty cycle \leq 2%.

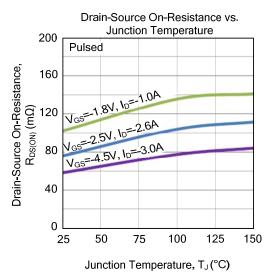
■ TYPICAL CHARACTERISTICS

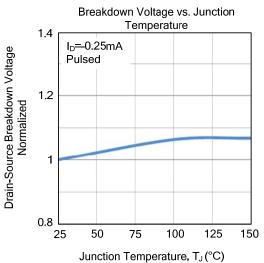




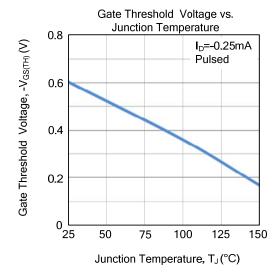


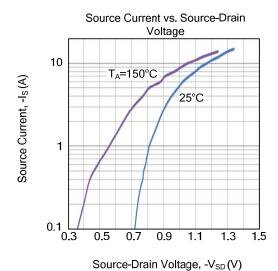


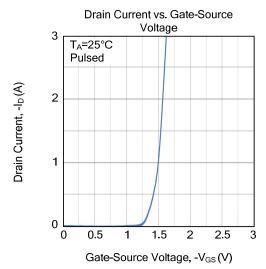




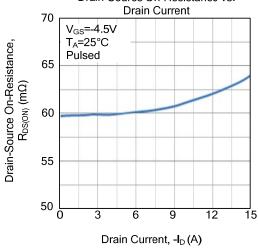
■ TYPICAL CHARACTERISTICS (Cont.)

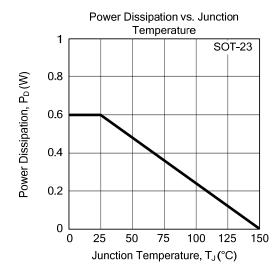


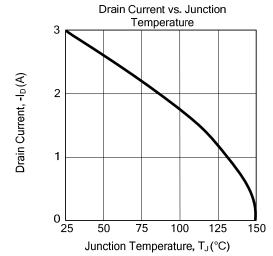




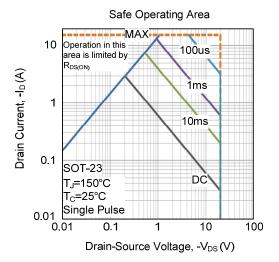








■ TYPICAL CHARACTERISTICS (Cont.)



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